

Bekir Gurbulak

List of Publications by Year in descending order

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55
papers

1,144
citations

394421

19
h-index

414414

32
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55
all docs

55
docs citations

55
times ranked

1356
citing authors

#	ARTICLE	IF	CITATIONS
1	The influence of chemical reactivity of surface defects on ambient-stable InSe-based nanodevices. <i>Nanoscale</i> , 2016, 8, 8474-8479.	5.6	92
2	Liquid-Phase Exfoliated Indium Selenide Flakes and Their Application in Hydrogen Evolution Reaction. <i>Small</i> , 2018, 14, e1800749.	10.0	90
3	Growth and characterization of Ag/n-ZnO/p-Si/Al heterojunction diode by sol-gel spin technique. <i>Journal of Alloys and Compounds</i> , 2013, 550, 129-132.	5.5	69
4	Indium selenide: an insight into electronic band structure and surface excitations. <i>Scientific Reports</i> , 2017, 7, 3445.	3.3	60
5	Temperature variation of current-voltage characteristics of Au/Ni/n-GaN Schottky diodes. <i>Physica E: Low-Dimensional Systems and Nanostructures</i> , 2009, 41, 646-651.	2.7	53
6	The Advent of Indium Selenide: Synthesis, Electronic Properties, Ambient Stability and Applications. <i>Nanomaterials</i> , 2017, 7, 372.	4.1	50
7	Temperature-dependent optical absorption measurements and Schottky contact behavior in layered semiconductor n-type InSe(:Sn). <i>Applied Surface Science</i> , 2007, 253, 3899-3905.	6.1	44
8	Liquid Phase Exfoliated Indium Selenide Based Highly Sensitive Photodetectors. <i>Advanced Functional Materials</i> , 2020, 30, 1908427.	14.9	42
9	Structural characterizations and optical properties of InSe and InSe:Ag semiconductors grown by Bridgman/Stockbarger technique. <i>Physica E: Low-Dimensional Systems and Nanostructures</i> , 2014, 64, 106-111.	2.7	39
10	Enhanced Electrocatalytic Activity in GaSe and InSe Nanosheets: The Role of Surface Oxides. <i>Advanced Functional Materials</i> , 2020, 30, 2005466.	14.9	35
11	The synthesis and characterization of sol-gel spin coated CdO thin films: As a function of solution molarity. <i>Materials Letters</i> , 2014, 126, 232-235.	2.6	34
12	The effects of the temperature and annealing on current-voltage characteristics of Ni/n-type 6H-SiC Schottky diode. <i>Microelectronic Engineering</i> , 2008, 85, 631-635.	2.4	31
13	Fabrication and characterization of Al ₂ ZnS ₄ heterojunction photodiodes. <i>Physica Status Solidi (A) Applications and Materials Science</i> , 2014, 211, 580-586.	1.8	31
14	The barrier-height inhomogeneity in identically prepared Ni/n-type 6H-SiC Schottky diodes. <i>Applied Physics A: Materials Science and Processing</i> , 2008, 91, 337-340.	2.3	26
15	Capacitance and conductance-frequency characteristics of Au-Sb/p-GaSe:Gd Schottky barrier diode. <i>Vacuum</i> , 2011, 85, 798-801.	3.5	26
16	Growth and Temperature Dependence of Optical Properties of Er Doped and Undoped n-Type InSe. <i>Japanese Journal of Applied Physics</i> , 1999, 38, 5133-5136.	1.5	25
17	The Urbach tails and optical absorption in layered semiconductor TlGaSe ₂ and TlGaS ₂ single crystals. <i>European Physical Journal D</i> , 2005, 55, 93-103.	0.4	23
18	Electric field influence on absorption measurement in InSe single crystal. <i>Physica E: Low-Dimensional Systems and Nanostructures</i> , 2003, 16, 274-279.	2.7	20

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19	Growth and optical properties of Dy doped and undoped n-type InSe single crystal. Solid State Communications, 1999, 109, 665-669.	1.9	19
20	Mass attenuation coefficients for n-type InSe, InSe:Gd, InSe:Ho and InSe:Er single crystals. Journal of Quantitative Spectroscopy and Radiative Transfer, 2005, 90, 399-407.	2.3	19
21	Urbach Tail and Optical Absorption in Layered Semiconductor TlGaSe ₂ (1-x)S ₂ Single Crystals. Physica Scripta, 2005, 72, 79-86.	2.5	19
22	Urbach tail and optical characterization of gadolinium-doped TlGaSe ₂ single crystals. Physica Scripta, 2008, 77, 025702.	2.5	19
23	Evaluation of Structural and Optical Properties of Mn-Doped ZnO Thin Films Synthesized by Sol-Gel Technique. Metallurgical and Materials Transactions A: Physical Metallurgy and Materials Science, 2012, 43, 5088-5095.	2.2	19
24	Absorption measurement and Urbach's rule in InSe and InSe:Ho _{0.0025} , InSe:Ho _{0.025} single crystals. Optical Materials, 2006, 28, 488-493.	3.6	18
25	Growth and Optical Properties of Ho Doped n-Type Indium Selenide. Physica Status Solidi A, 1998, 168, 495-500.	1.7	17
26	The optical investigation of TlGa _{0.999} Pr _{0.001} Se ₂ and TlGaSe ₂ single crystals. Physica B: Condensed Matter, 2001, 293, 289-296.	2.7	17
27	Temperature dependence of galvanomagnetic properties for Gd doped and undoped p-type GaSe. Journal of Applied Physics, 1998, 83, 2030-2034.	2.5	16
28	Measurement of mass attenuation coefficients for holmium doped and undoped layered semiconductors InSe at different energies and the validity of mixture rule for crystals around the absorption edge. Journal of Quantitative Spectroscopy and Radiative Transfer, 2006, 102, 343-347.	2.3	16
29	An investigation of Zn/ZnO:Al/p-Si/Al heterojunction diode by sol-gel spin coating technique. Journal of Sol-Gel Science and Technology, 2014, 71, 589-596.	2.4	16
30	Electrothermal investigation of the switching effect in p-Type TlInSe ₂ , TlInTe ₂ , and TlGaTe ₂ chain chalcogenide semiconductors. Journal of Electronic Materials, 1996, 25, 1054-1059.	2.2	13
31	Electrical characterization of Ag/p-GaSe:Gd schottky barrier diodes. Physica E: Low-Dimensional Systems and Nanostructures, 2010, 42, 1958-1962.	2.7	12
32	Effective mass calculation for InSe, InSe:Er crystals. Physica E: Low-Dimensional Systems and Nanostructures, 2007, 36, 217-220.	2.7	11
33	Urbach tail and electric field influence on optical properties of InSe and InSe:Er single crystals. Applied Physics A: Materials Science and Processing, 2008, 90, 479-485.	2.3	11
34	Structural and optical properties of ZnO thin films by the spin coating Sol-Gel method. Journal of Sol-Gel Science and Technology, 2011, 60, 66-70.	2.4	11
35	Silicon-doping influence on the crystalline, surface and optical features of cadmium oxide films deposited by sol-gel spin route. Optik, 2018, 165, 310-318.	2.9	11
36	Electrical characteristics and inhomogeneous barrier analysis of Au/Be/p-InSe: Cd Schottky barrier diodes. Microelectronic Engineering, 2009, 86, 106-110.	2.4	10

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37	Currentâ€“Voltage and Capacitanceâ€“Conductanceâ€“Voltage Characteristics of Al/SiO ₂ /p-Si and Al/Methyl Green (MG)/p-Si Structures. Metallurgical and Materials Transactions A: Physical Metallurgy and Materials Science, 2015, 46, 347-353.	2.2	10
38	Urbach Tail and Optical Investigations of Gd Doped and Undoped InSe Single Crystals. Physica Scripta, 2004, 70, 197-201.	2.5	9
39	Investigation of the electrical properties of Ho-doped InSe single crystal. Physica E: Low-Dimensional Systems and Nanostructures, 2004, 21, 85-90.	2.7	9
40	Absorption Measurements in InSe:Ho Single Crystal Under an Electric Field. European Physical Journal D, 2004, 54, 377-385.	0.4	7
41	Electrical properties of Al/pâ€“Ge and Al/Methyl Green/pâ€“Ge diodes. Philosophical Magazine, 2015, 95, 1646-1655.	1.6	7
42	The effect of Sn doping Urbach Tail and optical absorption measurements of InSe crystal. Journal of Physics: Conference Series, 2016, 707, 012027.	0.4	7
43	Analysis of temperature dependent current-voltage characteristics of Sn/p-GaTe/In Schottky diode. Optical Materials, 2022, 125, 112138.	3.6	7
44	Electric field influence on exciton absorption of Er doped and undoped InSe single crystals. Physica Scripta, 2007, 75, 424-430.	2.5	4
45	Fabrication and electrical characterization of Au/Pyronine-G/p-Si diode. Materials Science in Semiconductor Processing, 2014, 28, 20-25.	4.0	4
46	Effect of Temperature and Illumination on the Currentâ€“Voltage Characteristics of a Al/p-GaSe/In Diode. Journal of Electronic Materials, 2020, 49, 5698-5704.	2.2	4
47	The Growth of P-type TlGaSe ₂ (1-x)S _{2x} Single Crystals. European Physical Journal D, 2004, 54, 857-866.	0.4	3
48	Determination of Mass Attenuation Coefficients of Some Semiconductor and Biological Samples. Analytical Letters, 2010, 43, 1999-2008.	1.8	3
49	Lutentium incorporation influence on ZnO thin films coated via a solâ€“gel route: spin coating technique. Journal of Materials Science: Materials in Electronics, 2016, 27, 5089-5098.	2.2	2
50	Growth and structural characterizations of GaSe and GaSe:Cd single crystals. AIP Conference Proceedings, 2017, , .	0.4	2
51	Absorption Properties of Layer Semiconductor TlGaSe ₂ Doped Gd. Journal for Manufacturing Science and Production, 2001, 4, 113-120.	0.1	1
52	Growth, Optical and Electrical Properties of In ₂ S ₃ , In _{1-x} Cd _x S and CdS Thin Films by the (SILAR) Method. AIP Conference Proceedings, 2007, , .	0.4	1
53	Growth of InSe:Mn semiconductor crystals by Bridgmanâ€“Stockbarger technique and analysis of electron irradiation effects on Sn/InSe:Mn Schottky diodes. Radiation Effects and Defects in Solids, 2016, 171, 528-543.	1.2	0
54	Electrical characterization of In/p-GaSe:Cd/Auâ€“Ge single crystal grown by Bridgman/Stockbarger method. AIP Conference Proceedings, 2017, , .	0.4	0

#	ARTICLE	IF	CITATIONS
55	Effect of voltages on ^{137}Cs Ray linear attenuation coefficients for some semiconductors. Radiation Physics and Chemistry, 2021, 179, 109208.	2.8	0